

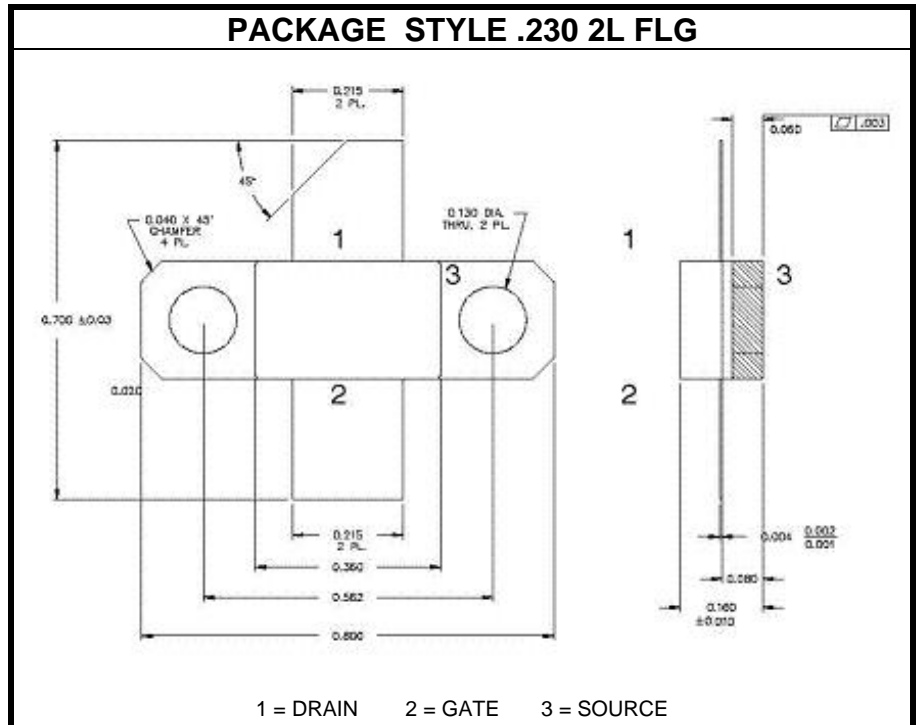
RF FIELD-EFFECT POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF9045LR1** is a high voltage, gold-metallized, laterally diffused metal oxide semiconductor. Ideal for today's RF power amplifier Applications.

MAXIMUM RATINGS

I_D	4.25 A
V_{DSS}	65 V
V_{GS}	-0.5, +15 V
P_{DISS}	117 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I _D = 200 μA	65			V
I_{DSS}	V _{DS} = 28 V V _{GS} = 0 V			75	μA
I_{GSS}	V _{DS} = 0 V V _{GS} = 5.0 V			1.3	μA
V_{GS(th)}	I _D = 400 μA V _{DS} = 10 V			4.8	V
V_{DS(on)}	I _D = 1.0 A V _{GS} = 10 V		0.25		V
g_{fs}	I _D = 1.0 A V _{DS} = 10 V		3.0		S
C_{iss}	V _{DS} = 28 V V _{GS} = 0 V f = 1.0 MHz		73		pF
C_{oss}			23		
C_{rss}			1.2		
G_L	V _{DS} = 28 V I _{DQ} = 450 mA P _{out} = 6 W f = 895 MHz	19	20		dB
P1dB	V _{DS} = 28 V 1 dB compression I _{DQ} = 450 mA f = 895 MHz	45	60		W
IMD	V _{DS} = 28 V I _{DQ} = 450 mA P _{OUT} = 45 W f = 895 MHz		31		dBc
IRL			10		dB